

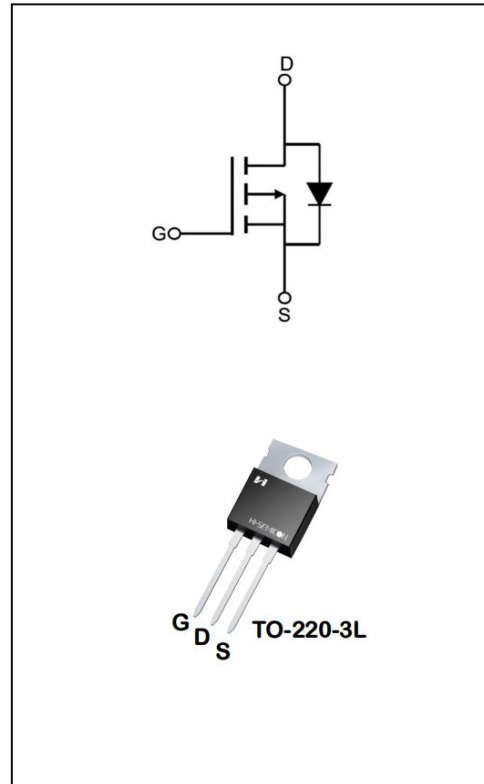
30A, 100V P-CHANNEL MOSFET

GENERAL DESCRIPTION

This power mosfet is an N-channel enhancement mode power MOS field effect transistor which is produced using Hi-semicon proprietary F-Cell™ structure VDMOS technology. These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

Features

- ◆  $V_{DS} = -100V, I_D = -30A$
- ◆  $R_{DS(on)}$   
TYP:  $18m\Omega @ V_{GS} = -10V$



ORDERING INFORMATION

| Part No.   | Package   | Marking    | Material | Packing |
|------------|-----------|------------|----------|---------|
| SFP10003PT | TO-220-3L | SFP10003PT | Pb Free  | Tube    |

### ABSOLUTE MAXIMUM RATINGS (T<sub>J</sub>=25°C unless otherwise noted)

| Characteristics   |                        | Symbol           | Ratings  | Unit |
|---|------------------------|------------------|----------|------|
| Drain-Source Voltage  |                        | V <sub>DS</sub>  | -100     | V    |
| Gate-Source Voltage   |                        | V <sub>GS</sub>  | ±20      | V    |
| Drain Current   | T <sub>C</sub> = 25°C  | I <sub>D</sub>   | -30      | A    |
|   | T <sub>C</sub> = 100°C |                  | -20      |      |
| Drain Current Pulsed(Note 1)  |                        | I <sub>DM</sub>  | -120     | A    |
| Power Dissipation(T <sub>C</sub> =25°C)<br>-Derate above 25°C                 |                        | P <sub>D</sub>   | 90       | W    |
| Single Pulsed Avalanche Energy (Note 2)                                       |                        | E <sub>AS</sub>  | 361      | mJ   |
| Operation Junction Temperature Range  |                        | T <sub>J</sub>   | -55~+150 | °C   |
| Storage Temperature Range   |                        | T <sub>stg</sub> | -55~+150 | °C   |
| Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds |                        | TL               | 260      | °C   |

### THERMAL CHARACTERISTICS

| Characteristics                         | Symbol           | MAX | Unit |
|---|------------------|-----|------|
| Thermal Resistance, Junction-to-Case    | R <sub>θJC</sub> | 1.5 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R <sub>θJA</sub> | 60  | °C/W |

### ELECTRICAL CHARACTERISTICS

| Characteristics                          | Symbol              | Test conditions   | Min. | Typ.  | Max. | Unit |
|--|---------------------|---|------|-------|------|------|
| Off Characteristics                      |                     |   |      |       |      |      |
| Drain -Source Breakdown Voltage          | B <sub>VDS</sub>    | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA   | -100 | --    | --   | V    |
| Drain-Source Leakage Current             | I <sub>DSS</sub>    | V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V   | --   | --    | -1   | uA   |
| Gate-Source Leakage Current              | I <sub>GSS</sub>    | V <sub>GS</sub> =20V, V <sub>DS</sub> =0V   | --   | --    | 100  | nA   |
| Gate-Source Leakage Current              | I <sub>GSS</sub>    | V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V  | --   | --    | -100 |      |
| On Characteristics                       |                     |   |      |       |      |      |
| Gate Threshold Voltage                   | V <sub>GS(th)</sub> | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> =-250μA  | -1.5 | -2.0  | -2.5 | V    |
| Static Drain- Source On State Resistance | R <sub>DSON</sub>   | V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A   | --   | 39    | 50   | mΩ   |
|  |                     | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A  | --   | 43    | 55   |      |
| Dynamic Characteristics                  |                     |   |      |       |      |      |
| Input Capacitance                        | C <sub>iss</sub>    | V <sub>DS</sub> =-25V<br>V <sub>GS</sub> =0V<br>f=1.0MHZ  | --   | 4620  | --   | pF   |
| Output Capacitance                       | C <sub>oss</sub>    |   | --   | 275   | --   |      |
| Reverse Transfer Capacitance             | C <sub>rss</sub>    |   | --   | 208   | --   |      |
| Switching Characteristics                |                     |   |      |       |      |      |
| Turn-on Delay Time                       | t <sub>d(on)</sub>  | V <sub>DD</sub> =-50V, V <sub>GS</sub> =-10V<br>R <sub>G</sub> =10Ω, I <sub>D</sub> =-15A<br>(Note 3.4) | --   | 10.2  | --   | ns   |
| Turn-on Rise Time                        | t <sub>r</sub>      |   | --   | 40.1  | --   |      |
| Turn-off Delay Time                      | t <sub>d(off)</sub> |   | --   | 265.3 | --   |      |
| Turn-off Fall Time                       | t <sub>f</sub>      |   | --   | 92.5  | --   |      |

|                    |          |  |    |      |    |    |
|--------------------|----------|--|----|------|----|----|
| Total Gate Charge  | $Q_g$    | $V_{DS}=-50V, I_D=-15A$<br>$V_{GS}=-10V$<br>(Note 3.4) | -- | 80.5 | -- | nc |
| Gate-Source Charge | $Q_{gs}$ |  | -- | 19.1 | -- |    |
| Gate-Drain Charge  | $Q_{gd}$ |  | -- | 14.7 | -- |    |

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Characteristics           | Symbol   | Test conditions   | Min. | Typ.  | Max. | Unit |
|---------------------------|----------|---|------|-------|------|------|
| Continuous Source Current | $I_S$    | Integral Reverse P-N<br>Junction Diode in the<br>MOSFET | --   | --    | -30  | A    |
| Pulsed Source Current     | $I_{SM}$ |   | --   | --    | -120 |      |
| Diode Forward Voltage     | $V_{SD}$ | $I_S=-15, V_{GS}=0V$                                    | --   | -0.82 | -1.2 | V    |
| Reverse Recovery Time     | $T_{rr}$ | $I_F=-15A$<br>$dI_F/dt=100A/\mu S$                      | --   | 36    | --   | ns   |
| Reverse Recovery Charge   | $Q_{rr}$ |   | --   | 52    | --   | nC   |

- 1.Pulse width limited by maximum junction temperature
- 2.L=0.5mH,  $V_{DD}=-50V, V_G=-10V, R_G=25\Omega$ , starting  $T_J=25^\circ C$
- 3.Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
- 4.Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. Output Characteristics

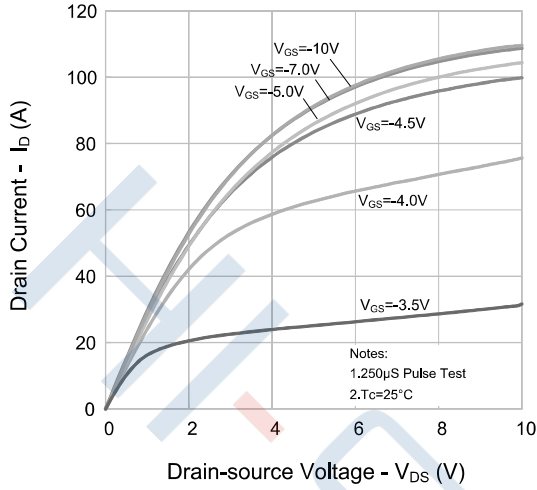


Figure 2. Transfer Characteristics

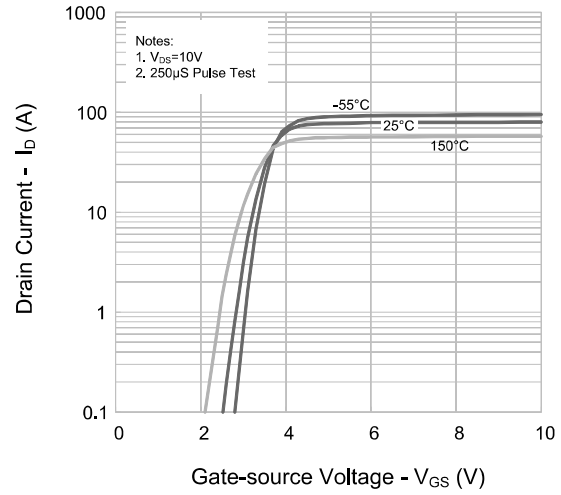


Figure 3. On-resistance vs. Drain Current

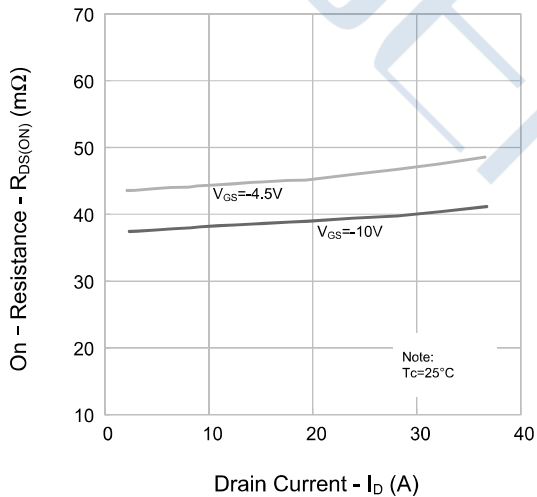


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

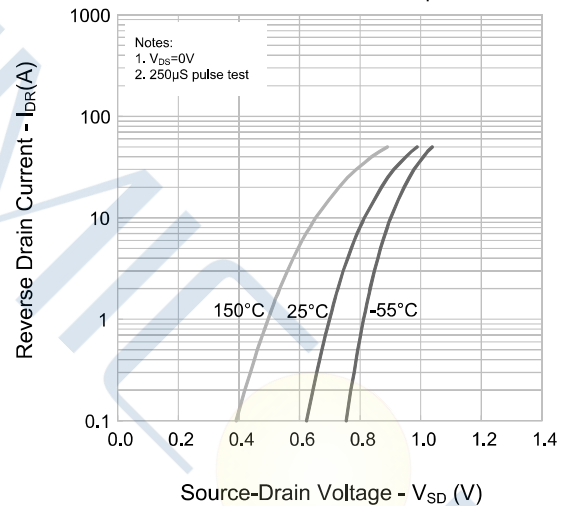


Figure 5. Capacitance Characteristics

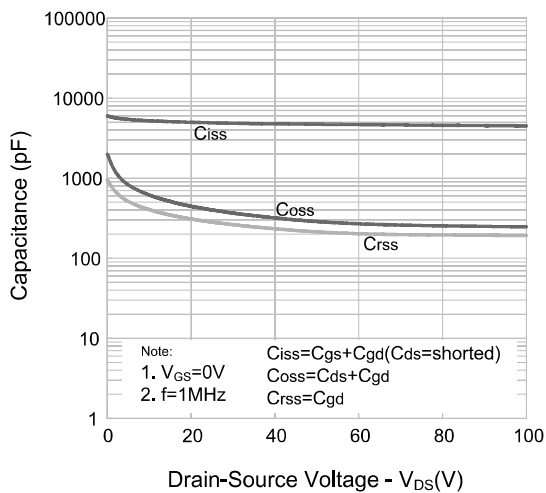
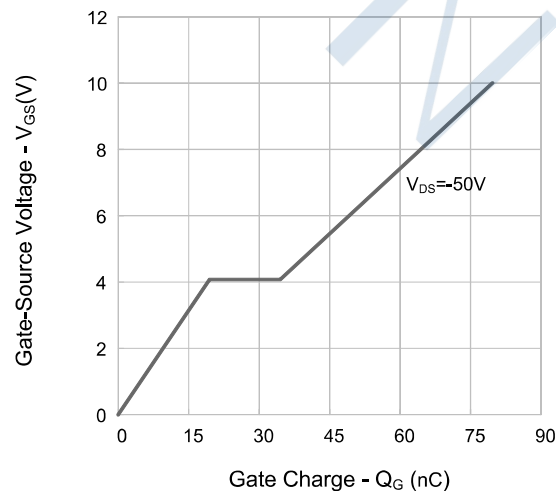


Figure 6. Gate Charge



Typical Performance Characteristics

Figure 7. Breakdown Voltage vs. Temperature Characteristics

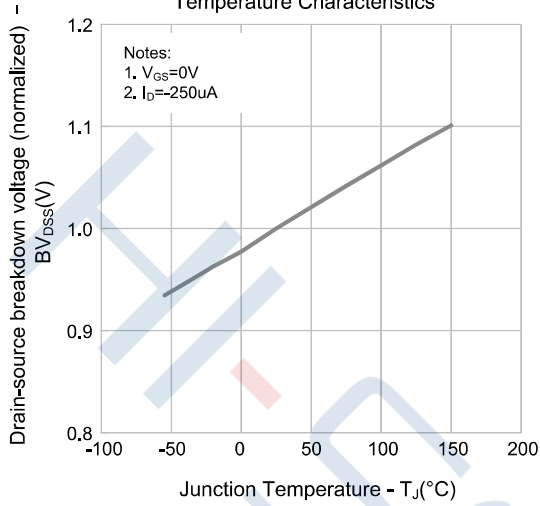


Figure 8. On-resistance vs. Temperature Characteristics

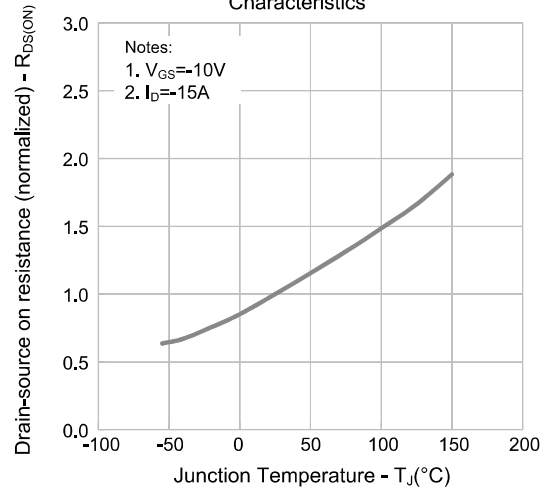
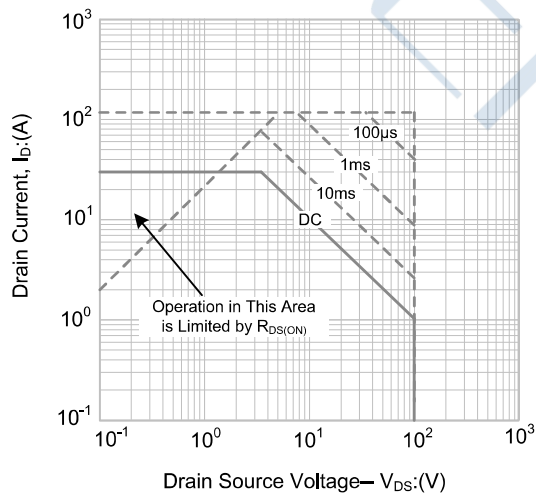
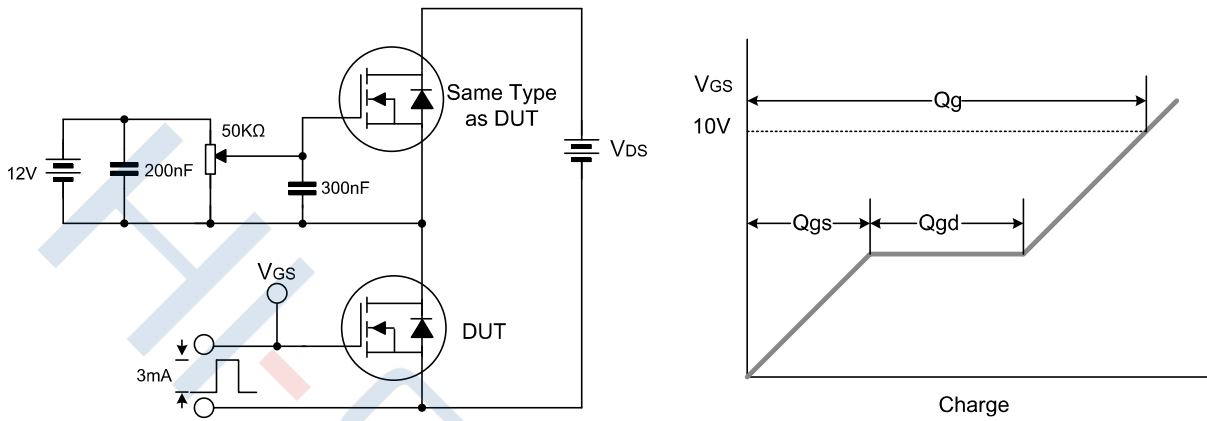


Figure 9. Max. Safe Operating Area

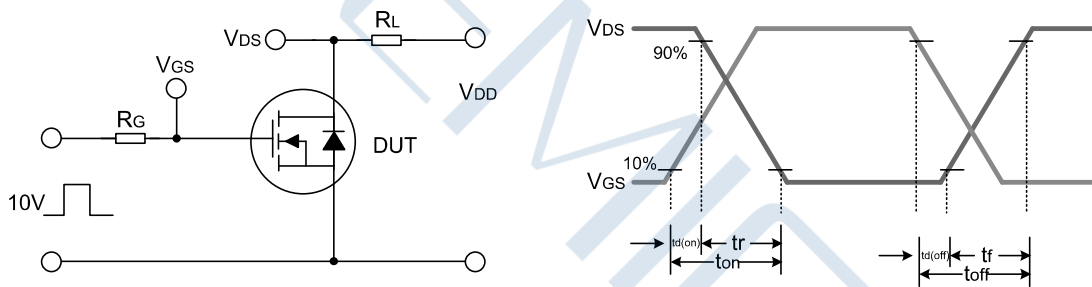


Test Circuit

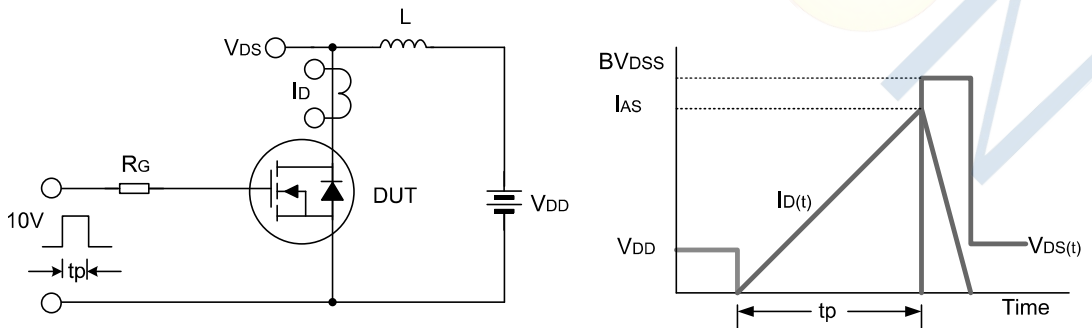
Gate Charge Test Circuit & Waveform



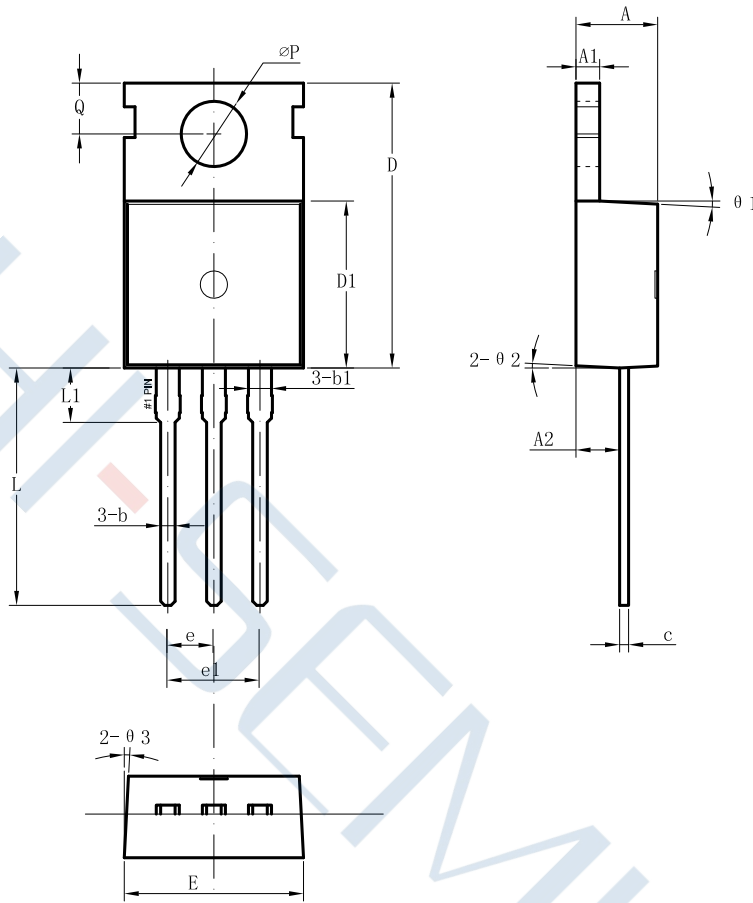
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Package Dimensions of TO-220-3L



| 符号         | 机械尺寸/mm |       |       |
|------------|---------|-------|-------|
|            | 最小值     | 典型值   | 最大值   |
| A          | 4.30    | 4.50  | 4.70  |
| A1         | 1.25    | 1.30  | 1.40  |
| A2         | 2.20    | 2.40  | 2.60  |
| b          | 0.70    | 0.80  | 0.95  |
| b1         |         | 1.27  |       |
| c          | 0.40    | 0.50  | 0.65  |
| D          | 15.20   | 15.70 | 16.20 |
| D1         | 9.00    | 9.20  | 9.40  |
| E          | 9.70    | 10.0  | 10.10 |
| e          |         | 2.54  |       |
| e1         |         | 5.08  |       |
| L          | 12.60   | 13.08 | 13.60 |
| L1         |         | 3.00  |       |
| $\phi P$   | 3.50    | 3.60  | 3.80  |
| Q          | 2.60    | 2.80  | 3.00  |
| $\theta 1$ |         | 3°    |       |
| $\theta 2$ |         | 3°    |       |
| $\theta 3$ |         | 3°    |       |

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